

L Number	Hits	Search Text	DB	Time stamp
1	17145	ESD (electrostatic near discharge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/06 08:59
2	28617	SCR (silicon near controll\$4 near rectifier)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/06 08:59
10	396167	trigger\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/06 09:37
12	708	(ESD (electrostatic near discharge)) and (SCR (silicon near controll\$4 near rectifier)) and trigger\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/06 09:38

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2	28617	SCR (silicon near controll\$4 near rectifier)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/06 08:59
5	158	(trigger\$3 near2 tap) trigger-tap	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/06 09:00
6	12	(ESD (electrostatic near discharge)) and (SCR (silicon near controll\$4 near rectifier)) and ((trigger\$3 near2 tap) trigger-tap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/04/06 09:00